

Part Number

Customer

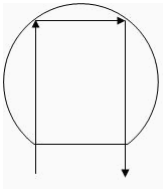
Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	150.00 +/- 0.50 mm	
	2.0 Notch or Flat	Notch	Wafer Vendor
	3.0 Notch Direction	{110} +/- 1 degree	Wafer Vendor
	4.0 Notch Depth Tolerance	1mm, -0mm / + 0.25mm	Wafer Vendor
	5.0 Notch Angle	90 degrees. +5, -1 degree	Wafer Vendor
	6.0 Overall Thickness	662.70 +/- 5.50 µm	ADE 100%
	7.0 Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0 Bow	<60.00µm	ADE to ASTM F534, 20%
	9.0 Warp	<60.00µm	ADE to ASTM F657, 20%
	10.0 Edge Chips	0	Bright Light, 100% (note 2)
	11.0 Edge Exclusion	5mm	
HandleSilicon	12.0 Handle Growth Method	FZ	Wafer Vendor
	13.0 Handle Orientation	{111} off 3.5 +/- 0.5 degree	Wafer Vendor
	14.0 Handle Thickness	658.00 +/- 5.00 µm	ADE, 100%
	15.0 Handle Doping Type	N	Wafer Vendor
	16.0 Handle Dopant	Phosphorous	Wafer Vendor
	17.0 Handle Resistivity	5000 - 10000 Ohmcm	Wafer Vendor
	18.0 Backside Finish	Lapped and etched with oxide and lasermark	Wafer Vendor
BuriedOxide	19.0 Oxide Type	Thermal	
	20.0 Oxide Thickness	22,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	21.0 Oxide formed on	2 um on Handle Wafer and 0.2 um on device	
DeviceSilicon	22.0 Device Growth Method	CZ	Wafer Vendor
	23.0 Device Orientation	{111} off 2.5 +/- 0.5 degree	Wafer Vendor
	24.0 Nominal Thickness	2.50 +/- 0.50 µm	FTIR, 100% 9-Pt (note3)
	25.0 Distance to device silicon edge from wafer edge	< 2 mm	Guaranteed by Process
	26.0 Device Doping Type	N	Wafer Vendor
	27.0 Device Dopant	Arsenic	Wafer Vendor
	28.0 Device Resistivity	< 0.0025 Ohm-cm	Wafer Vendor
	29.0 Aluminium Level	<1E13 Atoms/cm3 Aluminium guaranteed by SIMS.	Wafer Vendor
	30.0 Boron Level	<1E14 Atoms/cm3 Boron content is checked on frequent basis and guaranteed by technology repeatability.	Wafer Vendor
	31.0 Buried Layer Implant	none	implant vendor
	32.0 Voids	0	Bright Light, 100% (note 2)

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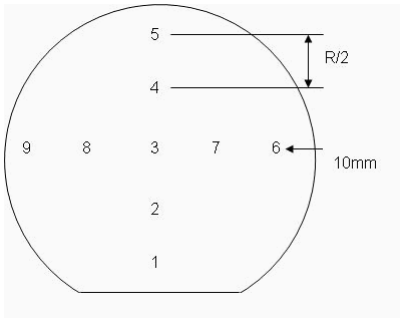
Category		Parameter	Specification	Measurement Method
DeviceSilicon	33.0	Scratches	0	Bright Light, 100% (note 2)
	34.0	Haze	none	Bright Light, 100% (note 2)

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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information